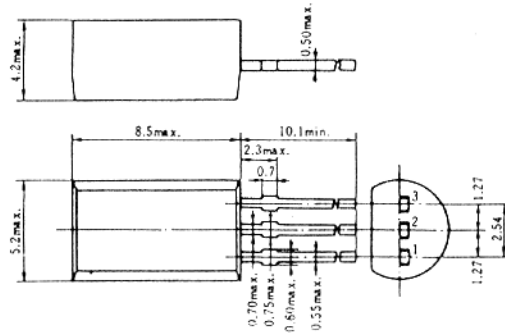
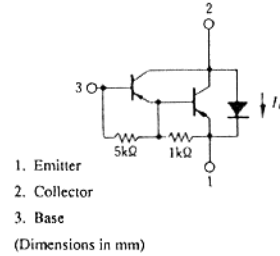


2SB1387

SILICON PNP EPITAXIAL
 LOW FREQUENCY POWER AMPLIFIER
 Complementary pair with 2SD1978



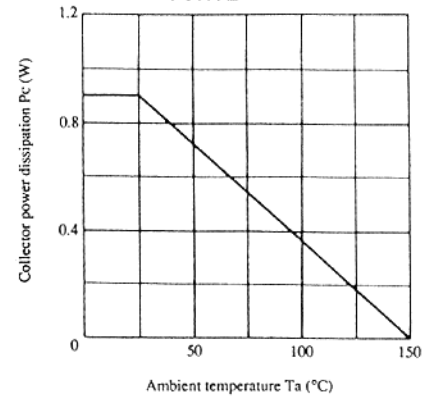
(JEDEC TO-92 MOD.)



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C)

Item	Symbol	2SB1387	Unit
Collector to base voltage	V _{CB0}	-120	V
Collector to emitter voltage	V _{CEO}	-120	V
Emitter to base voltage	V _{EBO}	-7	V
Collector current	I _C	-1.5	A
Collector peak current	i _{C(peak)}	-3.0	A
C to E diode forward current	I _D	1.5	A
Collector power dissipation	P _C	0.9	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

MAXIMUM COLLECTOR DISSIPATION CURVE



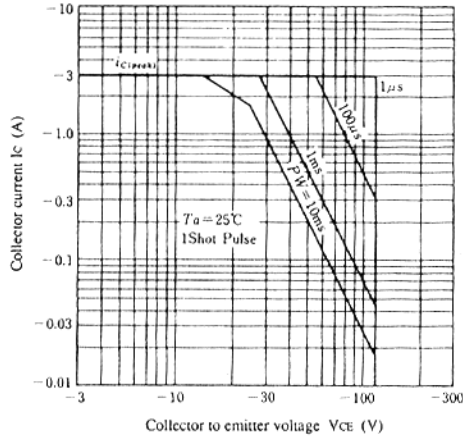
■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

Item	Symbol	Test Condition	min.	typ.	max.	Unit
Collector to base breakdown voltage	V _{(BR)CBO}	I _C = -0.1mA, I _E = 0	-120	—	—	V
Collector to emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA, R _{BE} = ∞	-120	—	—	V
Emitter to base breakdown voltage	V _{(BR)EBO}	I _E = -50mA, I _C = 0	-7	—	—	V
Collector cutoff current	I _{CBO}	V _{CB} = -100V, I _E = 0	—	—	-1	μA
	I _{CEO}	V _{CE} = -100V, R _{BE} = ∞	—	—	-10	μA
DC current transfer ratio	h _{FE}	V _{CE} = -3V, I _C = -1A*	2000	—	10000	
Collector to emitter saturation voltage	V _{CE(sat)1}	I _C = -1A, I _B = -1mA*	—	—	-1.5	V
	V _{CE(sat)2}	I _C = -1.5A, I _B = -1.5mA*	—	—	-2.0	V
Base to emitter saturation voltage	V _{BE(sat)1}	I _C = -1A, I _B = -1mA*	—	—	-2.0	V
	V _{BE(sat)2}	I _C = -1.5A, I _B = -1.5mA*	—	—	-2.5	V
C to E diode forward voltage	V _D	I _D = 1.5A*	—	—	3.0	V

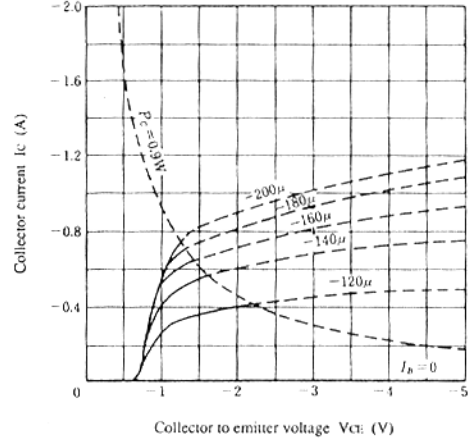
* Pulse Test

2SB1387

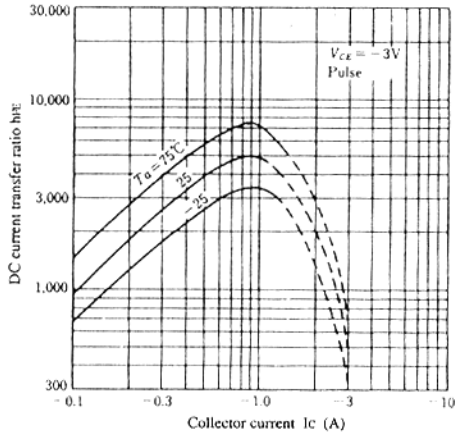
AREA OF SAFE OPERATION



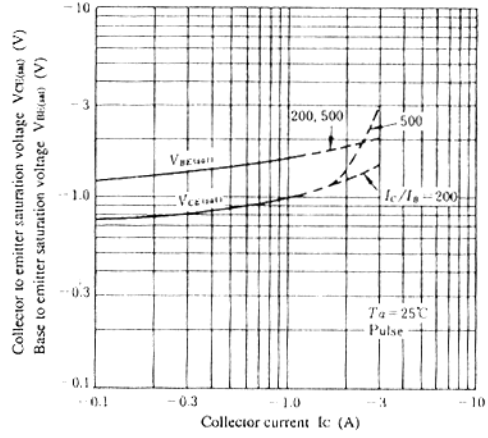
TYPICAL OUTPUT CHARACTERISTICS



DC CURRENT TRANSFER RATIO VS. COLLECTOR CURRENT



SATURATION VOLTAGE VS. COLLECTOR CURRENT



TRANSIENT THERMAL RESISTANCE

